

12V, 10A, Synchronous Boost Converter

1 Features

- Input Voltage Range :2.7V to 12V
- Output Voltage Range: 4.5V to 13.5V
- Efficiency up to 97%: VIN = 7.2 V, VOUT = 12 V, IOUT = 2 A
- Integrated 12mR switching FET and 15mΩ rectifier FET
- Adjustable switching frequency up to 2.2MHz
- Resistor-programmable peak current limit up to 10 A for high pulse current
- 4ms built-in soft start time
- DCM Operation under light load
- Input Under-Voltage Lockout
- Over-Temperature Protection
- 2.0mmx2.5mm VQFN Package

2 Applications

- Portable POS terminal
- Bluetooth Speaker
- E-Cigarette
- Thunderbolt Interface
- USB Type-C Power Delivery

3 Description

The PL31001 is a 16V synchronous Boost converter. The PL31001 integrates two low Rdson resistance power power FETs: A $12m\Omega$ switching FET and a $15m\Omega$ rectifier FFT.

The device provides a high-efficiency and small-size power solution for portable equipment.

The PL31001 uses the adaptive constant off time peak current mode control. PL31001 has an internal feature to help improving light load efficiency. When output current is low, PL31001 will go into DCM mode.

The PL31001 includes configurable features include programmable cycle-by-cycle current limit and programmable switching frequency in PWM mode is adjustable from 200kHz to 2.2MHz.

The PL31001 also implements a built-in 4ms soft start function and an adjustable peak switch current limit function. In addition, the device provides cycle-by-cycle over-current protection, and thermal shutdown protection.

4 Typical Application Schematic

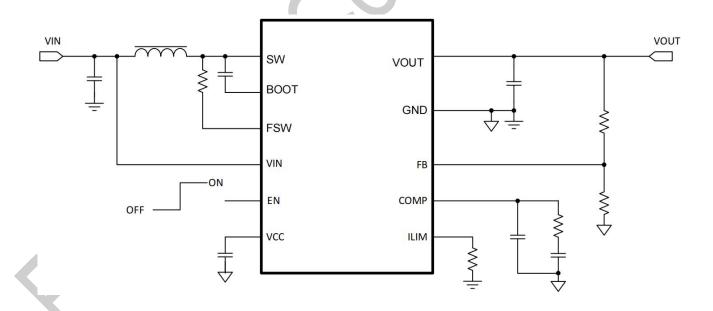


Fig. 4-1 Typical Application Schematic



5 Pin Configuration and Functions

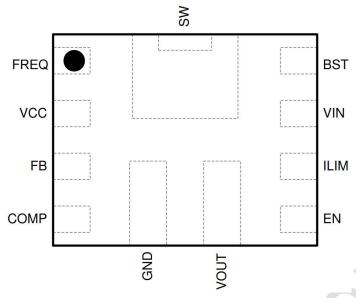


Fig. 5-1 Pin-Function

Pin		Description		
Number	Name	Description		
1	FREQ	The switching frequency is programmed by a resistor between this pin and the SW. This pin can't be float in application.		
2	vcc	Output of internal regulator, A ceramic capacitor of more than 4.7µF is required between this pin and ground.		
3	FB	Feedback Input. FB senses the output voltage, connect FB with a resistor divider connected between the output and ground. FB is a sensitive node, keep FB away from SW and BST pin.		
4	COMP	Output of internal error amplifier, loop compensation network connect to COMP and AGND .COMP is a sensitive node, keep COMP away from SW and BST pin.		
5	GND	Power ground.		
6	VOUT	Boost converter output.		
7	EN	Enable pin. Pull high to turn on the IC, don't float.		
8	ILIMIT	Adjustable LSFET peak current limit. Connect a resistor to AGND.		
9	VIN	Input supply pin. Bypass Vin to GND with a large capacitor and at least another 0.1uF ceramic capacitor to eliminate noise on the input to the IC. Put the capacitors close to Vin and GND pins.		
10	BST	Boot strap pin Connect a $0.1\mu F$ or greater capacitor between SW and BST to power the high side gate driver.		
11	sw	Power switching pin of boost converter, common node of LSFET drain and HSFET source. Connect the coil to this pin and power input.		

6 Device Marking Information

Order Information	Label Part NO.	Package	Package Qty	Top Marking	MSL
PL31001	PL31001IFQ11A	VQFN-2.0x2.5	3000	31001 RAAYMD	3

31001: Part Number

RAAYMD: RAA: Lot NO.; YMD: Package Date Code



7.1 Absolute Maximum Ratings(Note1)

Symbol	Description	Rating	Unit
BST	BST Voltage	-0.3 to SW+6.5	V
V _{VIN,} V _{SW,} V _{OUT}	VIN, SW, VOUT voltage	-0.3 to +20	V
Others	FB, COMP, ILIMIT, VCC, FREQ, EN voltage	-0.3 to +6.5	V

7.2 Handling Ratings

PARAMETER DEFINITION		MIN	MAX	UNIT
T _{ST}	Storage Temperature Range -		150	°C
T _J Junction Temperature			+150	°C
T _L Lead Temperature			+260	°C
V _{ESD}	HBM Human body model		2	kV
	CDM Charger device model		500	V

7.3 Recommended Operating Conditions (Note 2)

Symbol	Description	Rating	Unit
V _{IN}	Input Voltage	2.7 to 12	V
V _{OUT}	Output Voltage	4.5 to 13.5	V
V _{BST}	BST voltage	0 to SW+5	V
V _{SW}	SW voltage	0 to VOUT	V
Others	FB, COMP, ILIMIT, VCC, FREQ, EN voltage	0 to 5	V
T _A	Operating Ambient Temperature Range	-40 to +85	°C

7.4 Thermal Information(Note 3)

Symbol	Description	VQFN2.0x2.5	Unit	
θ _{JA}	Junction to ambient thermal resistance	53.4	°C/M	
θ _{JC(bot)}	Junction to case thermal resistance	0.7	°C/W	

Notes:

- 1) Exceeding these ratings may damage the device.
 2) The device function is not guaranteed outside of the recommended operating conditions.
 3) Measured on approximately 1" square of 1 oz copper.



7.5 Electrical Characteristics

VIN = 2.7 V to 5.5 V and VOUT = 9 V, TJ = -40 °C to 125 °C, Typical values are at TJ = 25 °C, unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Supply Se	ection	1				
V _{IN}	VIN operating range		2.7		12	V
V _{INUV}	VIN UVLO threshold voltage	when VIN < V _{INUV} , IC turn off, falling edge		2.5		V
V _{INUV_HYS}	VIN UVLO hysteresis voltage	after VIN > V _{INUV} + V _{INUV_HYS} , IC restore operation		0.22		٧
Vcc	VCC regulation voltage	I _{VCC} =2mA, VIN=6V		4.9		٧
V _{CCUV}	VCC UVLO threshold voltage	VCC falling edge		2.1		٧
V _{CCUV_HYS}	VCC UVLO hysteresis voltage			0.1		٧
I _{Q_VIN}	Standby current into VIN pin	VIN=EN=4V, VOUT=12V, FB=1.3V, no Ext. FET		8.5		uA
I _{Q_VOUT}	Standby current into VOUT pin	VIN=EN=4V, VOUT=12V, FB=1.3V, no Ext. FET		120		uA
I _{SD_VIN}	Shutdown current	EN=0V, VIN=4V		1		uA
VOUT See						
V out	VOUT operating range		4.5		13.5	٧
V_{FB}	Reference voltage at FB pin			1.2		٧
Error Am	plifier Section					
G _M	Error amplifier trans-conductance	FB=1.2V, COMP=1.5V		190		uS
I _{SOURCE}	COMP pin source current			30		uA
I _{SINK}	COMP pin sink current			30		uA
G _{CS}	COMP to current gain(Note4)			10		S
Power FE	T Section					
Ronls	Low side NFET on-resistance	I _{DS} =0.5A		12		mΩ
R _{ONHS}	High side NFET on-resistance	I _{DS} =0.5A		15		mΩ
I _{LKLS}	Low side FET leakage current	VSW=12V		1		uA
I _{LKHS}	High side FET leakage current	VOUT=12V, VSW=0V		1		uA
V _{BST}	High side driver supply voltage	BST-SW		5		٧
ILIM Sect	ion					
VILIM	Reference voltage at ILIM			0.5		٧
	Deale I C NICET annual times	RLIM=75k Ohm, Ilimit=750K/RSET		10		Α
I _{LIM}	Peak LS NFET current limit	RLIM=150k Ohm, Ilimit=750K/RSET		5		Α
Fsw Secti	ion					
f _{SW}	Switching frequency	RFREQ=300k, Fs = 15x10^10/RFREQ		500		kHz
t _{on_min}	Minimum LSFET on time(Note4)			120		ns
t _{off_min}	Minimum HSFET on time(Note4)			335		ns
EN section	<u> </u>	1	<u> </u>	1		
V _{EN_H}	EN high threshold voltage	EN > V _{EN_H} , enable IC after t _{EN_ON}		1.2		V
V _{EN_L}	EN low threshold voltage	EN < V _{EN_L} , shutdown IC		1.0		V
I _{EN}	EN input current	VEN=1.3V		500		nA



Electrical Characteristics(continued)

 $VIN = 2.7 V \text{ to } 5.5 V \text{ and } VOUT = 9 V, TJ = -40 ^{\circ}C \text{ to } 125 ^{\circ}C$, Typical values are at TJ = 25 $^{\circ}C$, unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit			
Soft Start	Soft Start section								
T _{STARTUP}	FB Soft Startup time			4		mS			
OTP sect	OTP section								
T _{SD}	Thermal shutdown temperature			150		° C			
T _{SD_HYS}	Thermal shutdown hysteresis temperature			20		° C			

Note:

1)Guaranteed by design, not tested in production.



8. Detailed Description

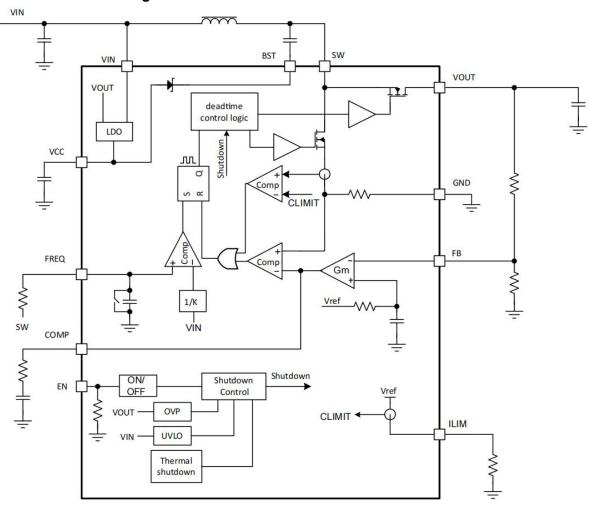
8.1 Overview

The PL31001 is a synchronous boost converter designed for delivering the switch peak current up to 10A and output voltage up to 13.5 V. PL31001 has an internal feature to help improving light load efficiency. When output current is low, PL31001 will go into DCM mode.

The PL31001 provides the excellent line and load transient response with the minimal output capacitor. The external loop compensation brings the flexibility to use a wider range of the inductor and output capacitor combinations.

The PL31001 supports the adjustable switching frequency up to 2.2MHz. The device implements a programmable cycle-by-cycle current limit to protect the device from overload during the boost operation phase. The PL31001 triggers the hiccup short protection if the output current further increases and exceeds the short current threshold or the output voltage drops below the short threshold. And this device recovers automatically once the short condition releases.

8.2 Functional Block Diagram





8.3 Feature Description

8.3.1 Under-voltage Lockout

An under-voltage lockout (UVLO) circuit stops the operation of the converter when the input voltage drops below the UVLO threshold of 2.5 V. A hysteresis of 200 mV is added so that the device cannot be enabled again until the input voltage exceeds 2.7 V. This function is implemented in order to prevent malfunctioning of the device when the input voltage is between 2.5 V and 2.7 V.

8.3.2 Enable and Disable

When the input voltage is above UVLO rising threshold of 2.7 V and the EN pin is pulled high above 1.2 V, the PL31001 is enabled. When the EN pin is pulled below 1 V, the PL31001 goes into the shutdown mode and stops switching. The device stops switching in shutdown mode and consumes less than 3-µA current. Because of the body diode of the high-side rectifier FET, the input voltage goes through the body diode and appears at the VOUT pin at shutdown mode.

8.3.3 Startup

When the input voltage to the device exceeds the UVLO threshold and EN pin pulled to high as well, the PL31001 starts to ramp up the output voltage.

After the turn-on phase ends (typical 4 ms), The PL31001 regulates the FB pin to the internal soft start voltage and results in a gradual rise of the output voltage starting from the input voltage level to the target output voltage. The soft start time is typical 4 ms, which helps the regulator to gradually reach the steady state setting point, thus reducing the startup stresses and surges.

8.3.4 Adjustable Cycle-by-Cycle Switching Current Limit

When the PL31001 is in the normal boost switching phase, the device is prevented from the over current condition via the cycle by cycle current limit by sensing the current through the internal low-side FET. When the peak switch current triggers the current limit threshold, the low-side switch turns off to prevent the switching current further increasing.

The peak switch current limit can be set by a resistor connecting with the ILIMIT pin. The relationship between the current limit and the resistor is determined by Equation 1

$$R_{\text{LIMIT}} = \frac{750\text{K}}{I_{\text{LIMIT}}} \tag{1}$$

Where RLIMIT is the resistor for setting the current limit, with the unit of $k\Omega$, ILIMIT is switching peak current limit, with the unit of A. For instance, when the resistor value is 75 $k\Omega$, the switch peak current limit is 10 A.

8.3.5 Adjustable Switching Frequency

The PL31001 features of a wide adjustable switching frequency ranging up to 2.2MHz. The switching frequency is set by a resistor connected between the FSW pin and the SW pin. This pin cannot be left floating in the application. Use Equation 2 to calculate the resistor value for a desired frequency.

$$Freq = \frac{150000}{R_{Freq}} \text{ kHz}$$
 (2)

Where RFreq is the resistor for setting the frequency, with the unit of $k\Omega$, Freq is switching frequency, with the unit of kHz. For instance, when the resistor value is 300 $k\Omega$, the switching frequency is 500 kHz.

8.3.6 Bootstrap Voltage (BST)

The PL31001 has an integrated bootstrap regulator, and requires a small ceramic capacitor between the BST pin and SW



pin to provide the gate drive voltage for the high-side FET. The bootstrap capacitor is charged when the BST-SW voltage is below regulation. The value of this ceramic capacitor should be above 100 nF. A ceramic capacitor with an X7R or X5R grade dielectric with a voltage rating of 10 V or higher is recommended because of the stable characteristics over temperature and DC biased voltage.

8.3.7 Thermal Shutdown

A thermal shutdown is implemented to prevent the damage due to the excessive heat and power dissipation. Typically, the thermal shutdown occurs at the junction temperature exceeding 150°C. When the thermal shutdown is triggered, the device stops switching and recover when the junction temperature falls below 130°C(typical).

8.4 Device Functional Modes

PL31001 operates at the adaptive constant off time peak current mode control (CMCOT). At the beginning of each switching cycle, the low-side FET switch turns on, and the inductor current ramps up to a peak current that is determined by the output of the internal error amplifier. The PWM controller turns off the low-side FET when the peak inductor current reaches a threshold level set by the error amplifier output. After the low-side FET turns off, the high-side synchronous FET is turned on after a short dead time until the adaptive off timer end or until the inductor current reaches the reverse current sense threshold.

During the portion of the switching cycle when the low-side FET is on, the input voltage is applied across the inductor and stores the energy as the inductor current ramps up. Meanwhile only the output capacitor supplies the load current. When it turns off the low-side FET, the inductor transfers the stored energy via the high-side synchronous FET to replenish the output capacitor and also supply the load current. This operation repeats every switching cycle.



9 Application and Implementation

9.1 Setting the switching Frequency

The switching frequency of the PL31001 is set at 500 kHz. Use Equation 2 to calculate the required resistor value. For a target switching frequency of 500 kHz, The calculated value is 300 k Ω .

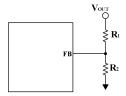
9.2 Setting the Cycle-By-Cycle Current Limit

The current limit of the PL31001 could be programmed by an external resistor. Use Equation 1 to calculate the required resistor value. For a target current limit of 10 A, the calculated resistor value is 75 k Ω .

9.3 Setting the Output Voltage

Choose R1 and R2 to program the proper output voltage. To minimize the power consumption under light load, it is desirable to choose large resistance values for both R1 and R2. A value between 10k and 1M is recommended for both resistors. If R1=200k is chosen, then R2 can be calculated to be:

$$V_{OUT} = V_{FB} \times \left(1 + \frac{R_1}{R_2}\right) \tag{3}$$



9.4 Selecting the Inductor

There are several considerations in choosing this inductor.

1) Choose the inductance to provide the desired ripple current. It is suggested to choose the ripple current to be about 40% of the maximum average input current. The inductance is calculated as:

$$L = \left(\frac{V_{IN}}{V_{OUT}}\right)^2 \times \frac{V_{OUT} - V_{IN}}{0.4 \times F_{SW} \times I_{OUT_MAX}}$$
(4)

Where F_{SW} is the switching frequency and $I_{OUT\ MAX}$ is the maximum load current.

PL31001 is less sensitive to the ripple current variations. Consequently, the final choice of inductance can be slightly off the calculation value without significantly impacting the performance.

2) The saturation current rating of an inductor must be selected to guarantee an adequate margin to the peak inductor current under full load conditions.

$$I_{SAT_MIN} > \frac{V_{OUT}}{V_{IN}} \times I_{OUT_MAX} + \left(\frac{V_{IN}}{V_{OUT}}\right)^2 \times \frac{V_{OUT} - V_{IN}}{2 \times F_{SW} \times L}$$
 (5)

3) The DCR of the inductor and the core loss at the switching frequency must be low enough to a chieve the desired efficiency requirement. It is desirable to choose an inductor with DCR<10mohm to achieve a good overall efficiency.

9.5 Selecting the Output Capacitors

The Boost Output capacitor CBD and disconnection FET Output capacitor COUT are selected to handle the output ripple noise requirements. Both steady state ripple and transient requirements must be taken in to account when selecting these capacitors. For the best performance, it is recommended to use X5R or better grade ceramic capacitor with 25V rating and



more than 22uF capacitors

9.6 Selecting the Input Capacitors

Multilayer ceramic capacitors are an excellent choice for the input decoupling of the step-up converter as they have extremely low ESR and are available in small footprints. Input capacitors should be located as close as possible to the device. While a 22-µF input capacitor is sufficient for the most applications, larger values may be used to reduce input current ripple.

Take care when using only ceramic input capacitors. When a ceramic capacitor is used at the input and the power is being supplied through long wires, such as from a wall adapter, a load step at the output can induce ringing at the VIN pin. This ringing can couple to the output and be mistaken as loop instability or could even damage the part. Additional "bulk" capacitance (electrolytic or tantalum) in this circumstance, should be placed between CIN and the power source lead to reduce ringing that can occur between the inductance of the power source leads and CIN.

9.7 Selecting the Bootstrap Capacitor

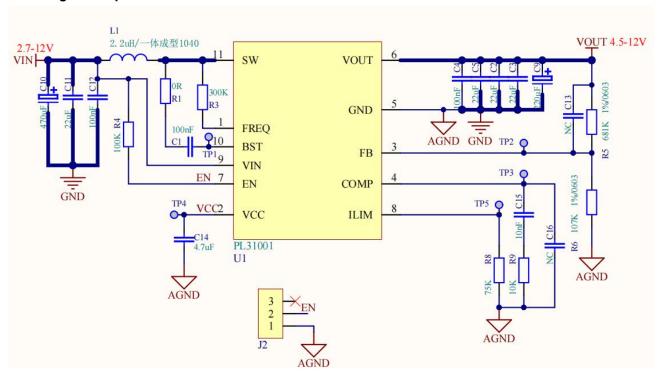
The bootstrap capacitor between the BST and SW pin supplies the gate current to charge the high-side FET device gate during each cycle's turn-on and also supplies charge for the bootstrap capacitor. The recommended value of the bootstrap capacitor is 0.1µF to 1µF. CBST should be a good quality, low ESR, ceramic capacitor located at the pins of the device to minimize potentially damaging voltage transients caused by trace inductance. A value of 0.1µF was selected for this design example.

9.8 Selecting the VCC Capacitor

The primary purpose of the VCC capacitor is to supply the peak transient currents of the driver and bootstrap capacitor as well as provide stability for the VCC regulator. The value of CVCC should be at least 10 times greater than the value of CBST, and should be a good quality, low ESR, ceramic capacitor. CVCC should be placed close to the pins of the IC to minimize potentially damaging voltage transients caused by the trace inductance. A value of 4.7 μ F was selected for this design example.



9.9 Design Example





10 PCB Layout

10.1 Layout Guidelines

The basic PCB board layout requires a separation of sensitive signal and power paths. If the layout is not carefully done, the regulator could suffer from the instability or noise problems.

The checklist below is suggested that be followed to get good performance for a well-designed board:

- 1. Minimize the high current path including the switch FET, rectifier FET, and the output capacitor. This loop contains high di/dt switching currents and easy to transduce the high frequency noise;
- 2. Minimize the length and area of all traces connected to the SW pin, and always use a ground plane under the switching regulator to minimize inter plane coupling;
- 3. Use a combination of bulk capacitors and smaller ceramic capacitors with low series resistance for the input and output capacitors. Place the smaller capacitors closer to the IC to provide a low impedance path for decoupling the noise;
- 4. The ground area near the IC must provide adequate heat dissipating area. Connect the wide power bus (e.g., VOUT, SW, GND) to the large area of copper, or to the bottom or internal layer ground plane, using vias for enhanced thermal dissipation;
- 5. Place the input capacitor being close to the VIN pin and the PGND pin in order to reduce the input supply ripple;
- 6. Place the noise sensitive network like the feedback and compensation being far away from the SW trace;
- 7. Use a separate ground trace to connect the feedback, compensation, frequency set, and the current limit set circuitry. Connect this ground trace to the main power ground at a single point to minimize circulating currents.

10.2 Layout Example

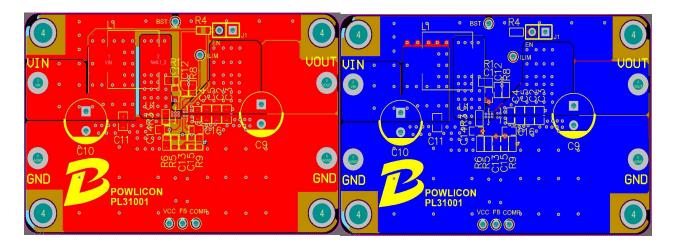
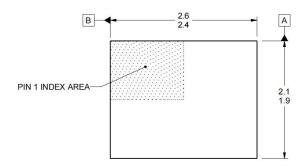
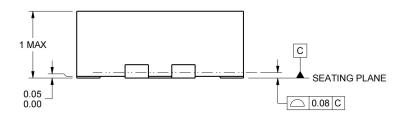


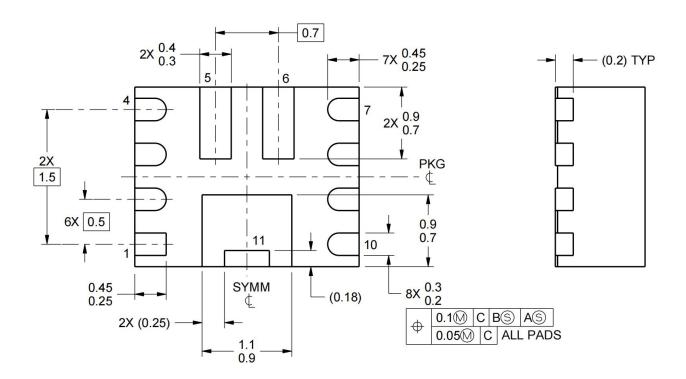
Fig. 10-2-1 PCB



11 Packaging Information







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